life.augmented

presented by EBV Elektronik | An Avnet Company |

STPOWER SiC MOSFET

The real breakthrough in high-voltage switching

Silicon Carbide: The Enabling Technology for higher power density in Industrial and Automotive application

Based on the advanced and innovative properties of wide bandgap materials, ST's STPOWER SiC MOSFETs feature very low $R_{DS(on)}$ per area, with the new SCT*N65G2 650 V and the new SCT*N120G2 1200 V product family, combined with excellent switching performance, reserve efficient and compact designs. These new families feature the industry's highest temperature rating of 200 °C for improved thermal design of power electronics systems.

KEY FEATURES

- Very low switching losses
- Low power losses at high temperatures
- Higher operating temperature (up to 200 °C)
- Body diode with no recovery losses
- Easy to drive

KEY BENEFITS

- Smaller form factor and higher power density
- Reduced size/cost of passive components
- Higher system efficiency
- Reduced cooling requirements and heatsink size

KEY APPLICATIONS

- Traction inverter
- EV charge station
- Photovoltaics
- Factory automation
- Motor drive
- Data center power supply
- OBC & DC/DC converter

SiC MOSFET VERSUS SILICON TRANSISTOR

Table 1 compares the new ST's second generation 650 V, 55 mΩ SCTH35N65G2V-7 STPOWER SiC MOSFET with a trench field-stop (TFS) IGBT of the same voltage rating and equivalent on-state resistance. The STPOWER SiC MOSFET exhibits significantly reduced switching losses, even at high temperatures. This enables designers to operate at very high switching frequencies, reducing the size of passive components for smaller form factors. In addition, for the STPOWER SiC MOSFET the variation of E_{ON} and E_{OFF} with temperature is very small. As an example, the E_{OFF} of the STPOWER SiC MOSFET remains basically unchanged as the temperature rises from 25 °C to 175 °C, while the E_{OFF} of the IGBT increases by the 89%. Even the change in resistance as the temperature rises is very low and lower than the competition, as shown in Figure 1.

Figure 1. normalized on-state resistance vs temperature

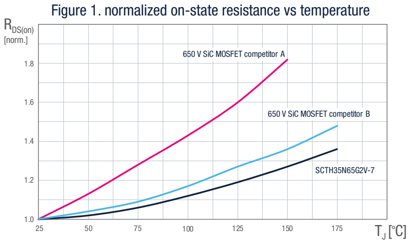

Table 1: Switching loss comparison

Device	V_{on} typ. (V) @ 25 °C, 20 A	V_{on} typ. (V) @ 175 °C, 20 A	$E_{on\text{-}typ}$ (µJ) @ 20 A, 400 V 25 °C / 175 °C	$E_{off\text{-}typ}$ (µJ) @ 20 A, 400 V 25 °C / 175 °C	E_{tot} rise with temperature	Die size (Normalized)
SCTH35N65G2V-7	1.1	1.48	100 / 100	35 / 35	negligible variation vs. Temperature	0.53
30 A, 650 V TFS IGBT	1.45	1.55	240 / 450	205 / 390	+89% from 25 °C to 175 °C	1.00

Note: Von measured @ VGS-SiC=18 V, VGE-IGBT=15 V - Eon includes the reverse recovery of the diode

STPOWER SiC MOSFET: 650 V Gen2

Part Number	V_{DS} (V)	$R_{DS(ON)}$ Typ @ 25° C (Ω)	I_D (A)	Package			
				HiP247	HiP247-LL	HiP247-4LL	H2PAK-7L
				T_J MAX= 200°C			T_J MAX= 175°C
SCTx35N65G2V	650	0.55	45	X	X		
SCTWA35N65G2V-4*						X	
SCTH35N65G2V-7							X
SCTW35N65G2VAG*				X			
SCTH35N65G2V-7AG							X
SCTx90N65G2V	650	0.018	119	X	X		
SCTWA90N65G2V-4*						X	
SCTH90N65G2V-7							X
SCTW100N65G2AG		0.020	100	X			
SCTH100N65G2-7AG							X

* Datasheet available on line within Q3 2020

STPOWER SiC MOSFET: 1200 V Gen2

Part Number	V_{DS} (V)	$R_{DS(ON)}$ Typ @ 25° C (Ω)	I_D (A)	Package			
				HiP247	HiP247-LL	HiP247-4LL	H2PAK-7L
				T_J MAX= 200°C			T_J MAX= 175°C
SCTW40N120G2VAG	1200	0.075	33	X			
SCTW40N120G2V*		0.070	45	X			
SCTWA40N120G2V-4*						X	
SCTW60N120G2AG		0.045	60	X			
SCTW70N120G2V		0.025	95	X			
SCTWA70N120G2V-4*						X	

* Datasheet available on line within Q3 2020

CONTACT
EBV Elektronik GmbH & Co. KG
D-85586 Poing
Im Technologiepark 2-8
Phone: +49 (0)8121 774-0
Fax: +49 (0)8121 774-422